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## U.S. UTILITY Patent Application

PATENT NUMBER and  
ISSUE DATE

APPL NUM 10002031	FILING DATE 11/30/2001	CLASS 438	SUBCLASS	GAU 2812	EXAMINER
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**\*APPLICANTS:** Yeo Yee-Chia; Chieh Lin Chun; Yang Fu-Liang; Hu Chen Ming;

**\*\*CONTINUING DATA VERIFIED:**

**\*\*FOREIGN APPLICATIONS VERIFIED:**

PG-PUB ☒ DO NOT PUBLISH ☒ RESCIND ☐

Foreign priority claimed ☐ yes ☒ no

US USC 119 conditions met ☐ yes ☒ no

Verified and Acknowledged Examiner's initials

ATTORNEY DOCKET NO  
TS01-1132

TITLE : Complementary metal oxide semiconductor transistor technology using selective epitaxy of a strained silicon germanium layer

<b>NOTICE OF ALLOWANCE MAILED</b>		<b>CLAIMS ALLOWED</b>	
		Total Claims	Print Claim for O.G.
<b>ISSUE FEE</b>		<b>DRAWING</b>	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg. Print Fig.
<input type="checkbox"/> <b>TERMINAL DISCLAIMER</b>		Primary Examiner	
		Application Examiner	
<b>PREPARED FOR ISSUE</b>		<b>WARNING:</b> The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.	

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